

## C. Materials Growth & Characterization 분과

2017년 2월 15일 (수), 08:30-10:00  
Room G (코럴, 3층)

### [WG1-C] Materials Growth & Characterization I

좌장: 송진동(한국과학기술원), 천승현(세종대학교)

<b>WG1-C-1</b> 08:30-08:45	<b>Study on the Wafer Warpage Due to Multi-Layer Film for 3D NAND</b> Byung-Wook Nam <sup>1,2</sup> , Sung-Young Lee <sup>1</sup> , Ki-Sang Lee <sup>1</sup> , Sung-Wook Lee <sup>1</sup> , Chung-Hyun Lee <sup>1</sup> , Ja-Young Kim <sup>1</sup> , and Jea-Gun Park <sup>2</sup> <i><sup>1</sup>Technology Development Center, LG Siltron, <sup>2</sup>Department of Electronics and Computer Engineering, Hanyang University</i>
<b>WG1-C-2</b> 08:45-09:00	<b>Synthesis of Single-Crystalline Tungsten Ditelluride (WTe<sub>2</sub>) Nanostructures Using Eutectic Metal Alloys</b> Jong Hwa Lee, Jinsung Kwak, Seunguk Song, Yongsu Jo, Se-Yang Kim, Hyung Duk Yun, and Soon-Yong Kwon <i>School of Materials Science and Engineering and Low Dimensional Carbon Materials Center, Ulsan National Institute of Science and Technology</i>
<b>WG1-C-3</b> 09:00-09:15	<b>Facile Observation of Intrinsic Graphene Defects of Different Origins through Selective Oxygen Transport</b> Yongsu Jo <sup>1</sup> , Jinsung Kwak <sup>1</sup> , Soon-Dong Park <sup>1</sup> , Na Yeon Kim <sup>1</sup> , Se-Yang Kim <sup>1</sup> , Zonghoon Lee <sup>1</sup> , Sung Youb Kim <sup>2</sup> , and Soon-Yong Kwon <sup>1,2</sup> <i><sup>1</sup>School of Materials Science and Engineering &amp; Low-Dimensional Carbon Materials Center, <sup>2</sup>School of Mechanical and Nuclear Engineering, Ulsan National Institute of Science and Technology</i>
<b>WG1-C-4</b> 09:15-09:30	<b>N-Doped Graphene Synthesis on SiC Substrate by Excimer Laser Annealing</b> Tae Hong Im, Insung Choi, and Keon Jae Lee <i>Department of Materials Science and Engineering, KAIST</i>
<b>WG1-C-5</b> 09:30-09:45	<b>Flat GaAs Epitaxial Layers grown on Si (001) Substrates with Nanoscale Strained Layer by MOCVD</b> In-Geun Lee <sup>1,2</sup> , Young-Dae Cho <sup>1,2</sup> , Dae-Hong Ko <sup>1</sup> , Sewoung Oh <sup>2</sup> , Yong-Ha Kim <sup>2</sup> , Young Su Choi <sup>2</sup> , Gyu-Beom Lee <sup>2</sup> , Chan-Soo Shin <sup>2</sup> , Won-Kyu Park <sup>2</sup> , Do Sun Lee <sup>3</sup> , and Dong Soo Lee <sup>3</sup> <i><sup>1</sup>Department of Materials Science and Engineering, Yonsei University, <sup>2</sup>Korea Advanced Nano Fab Center, <sup>3</sup>Semiconductor R&amp;D Center, Samsung Electronics Co., Ltd.</i>
<b>WG1-C-6</b> 09:45-10:00	<b>Precise Controllable Growth of Graphene Layer and Fine Pattern by Using MgO and Ni Hetero Catalyst</b> Aram Lee, Jaeyeong Lee, Jin Heon Park, and Hak Ki Yu <i>Department of energy systems Research, Ajou University</i>